

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

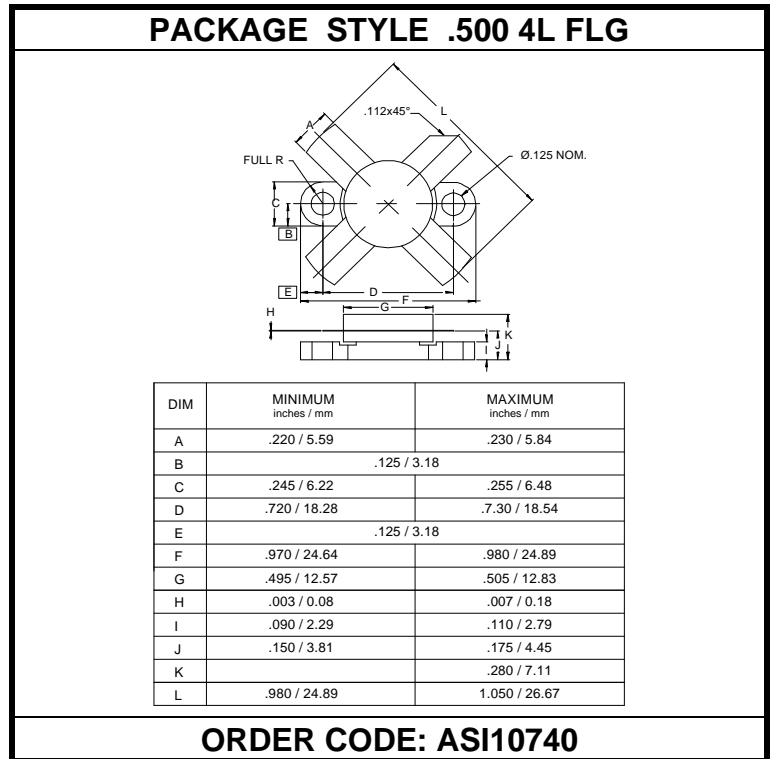
The ASI VLB100-12 is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CB0}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.65 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 50 mA	36			V
BV_{CES}	I _C = 100 mA	36			V
BV_{CEO}	I _C = 100 mA	18			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _{CE} = 12.5 V			15	mA
h_{FE}	V _{CE} = 5.0 V I _C = 5.0 A	20		---	---
C_{OB}	V _{CB} = 12.5 V f = 1.0 MHz			400	pF
P_G η_C	V _{CC} = 12.5 V P _{OUT} = 100 W f = 50 MHz	7.0	60		dB %